

Fine Ceramics for Electronics



Expanding Applications of Ceramic Components-1

Contributing to Down-sizing & Improved Functionality of Electronics

The electronics industry is continuously making remarkable progress and development. Kyocera, with its Fine Ceramics material and processing technologies developed during its history, supports the increased functionality of equipment used in a wide range of fields such as various electronic components and semiconductor devices along with equipment components required to support manufacturing.

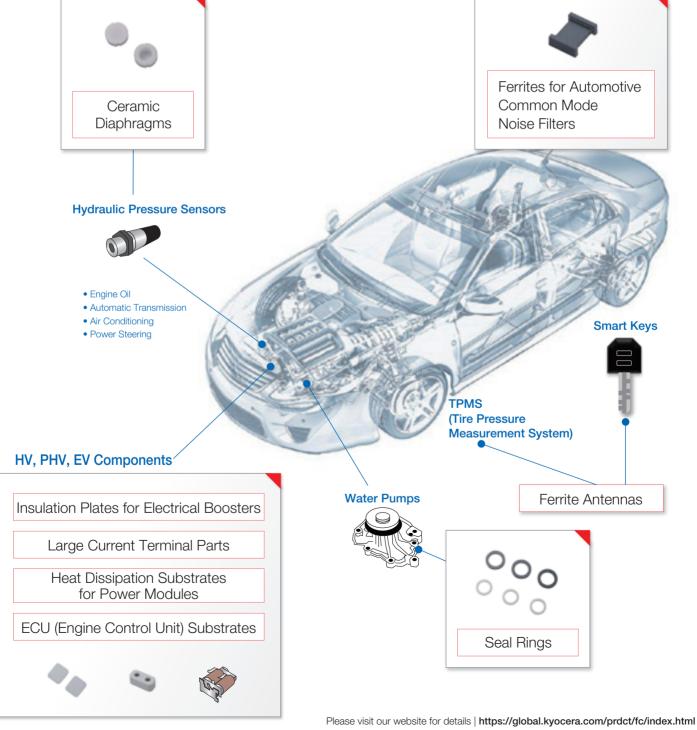




Expanding Applications of Ceramic Components-2

Enhancing Automotive Performance

Fine Ceramics provide excellent characteristics in mechanical strength at high temperature and electrical insulation. As automotive electronics evolve to require more robustness for long-term durability and safety to protect drivers and passengers, ceramic components are widely used in hybrid vehicles (HV/PHV) and electric vehicles (EV).





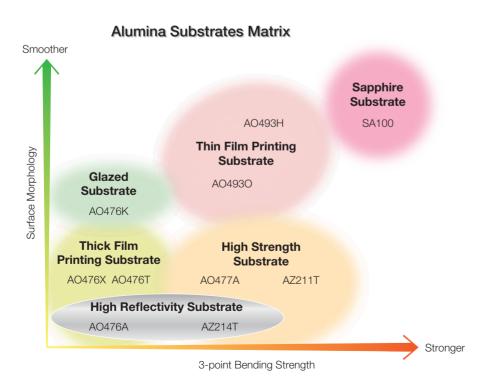
INDEX

1	Ceramic Substrates	05
		0.0
	Material Characteristics of Ceramic Substrates	_ 06
	Thick Film Printing Substrates	_ 08
	Alumina Metallized Substrates	_ 10
	Long Thick Film Printing Substrates	_ 10
	Thin Film Printing Substrates	_ 11
	Polished Thin Film Printing Substrates	_ 12
	Single Crystal Sapphire Substrates	_ 13
	High Reflectivity Alumina Substrates	_ 14
	Laser Cutting Design Guideline (Reference)	_ 15
	Glazing (Optional)	_ 16
2	Heat Dissipation Substrates	17
	Heat Dissipation Structure Ceramic Substrates	_ 18
	J.os.pano on aotaro conao casociato	0
3	Functional Materials	21
	Inductor Cores	_ 22
	Piezoelectric PZT Substrates	_ 25
4	Device Peripherals	27
		00
	Sapphire Cover Plates	_ 28
	Volume Production Components for Various Electronics	_ 29
	Ultra Thin Ceramic Caps	_ 30
	High Voltage-resistant Alumina Ceramic	32



Ceramic Substrates

Ceramic substrates are mainly used as hybrid IC substrates, thin film IC substrates, heat dissipation substrates, and LED sub-mount substrates. Our micro-grain material structure enables substrates which have a smooth surface with less voids, and high flexural strength and electrical insulation under high temperature environments. Upon request, we can also cut through-holes or scribe lines, or form electrode patterns (metallization) by printing or plating the substrates.







Material Characteristics of Ceramic Substrates

Main Applications			Thick Filn	n Printing	Thin Film	n Printing	Glazing	Pov (Hig		
Item	ltem Material			Alumina Al ₂ O ₃	Alumina Al ₂ O ₃	Alumina Al ₂ O ₃				
Materia	al Code			AO476X	AO476T	AO493O	AO493H	AO476K	AO477A	
Conter	nt		(%)	96	96	99.6	99.6	96	97	
Density	У	g/cm ³	JIS R 1634	3.70	3.78	3.86	3.96	3.70	3.79	
Ch Ch	Vickers Hardness HV9.807N	GPa	JIS R 1610	13.7	13.9	16.0	17.7	13.7	14.6	
Mechanical Characteristics	Flexural Strength 3 P.B.	MPa	JIS R 1601	310	380	550	550	350	480	
tics	Young's Modulus of Elasticity	GPa	JIS R 1602	330	340	390	390	330	340	
Thermal Characteristics	Coefficient of Linear Thermal Expansion (40-400°C)	×10 ⁻⁶ /K	JIS R 1618	7.2	7.0	7.2	7.2	7.2	7.0	
teristics	Thermal Conductivity 20°C	W/(m·K)	JIS R 1611	26	26	26	30	24	26	
	Dielectric Strength	kV/mm		12	15	15	18	15	16	
Electric Charac	Volume Resistivity 20°C	Ω·cm	JIS C 2141	>1014	>1014	>1014	>1014	>1014	>1014	
Electrical Characteristics	Dielectric Constant (1MHz)	_	100 0 2141	9.4	9.6	9.6	10.2	9.4	9.1	
	Dielectric Loss Tangent (1MHz)	(×10 ⁻⁴)		4.0	3.0	3.0	2.0	4.0	2.0	
Reflec (Wavel Thickr	tivity ength: 450nm) ness: 1mm	%	-	-	-	-	-	_	-	
Standard Specifications	Substrate Thickness	mm	-	0.15 ~1.016mm	0.32~2.7	0.1~1.0	<0.7	0.5~1.0	0.32~1.0	
ard cations	Surface Roughness		-	Ra0.2 ~0.8µm	Ra0.2 ~0.8μm	Ra0.05 ~0.08µm	<ra0.01µm (Mirror Surface)</ra0.01µm 	Ra0.2 ~0.3µm	Ra0.3 ~0.5µm	



dule igth)	LED Sub-mount Substrate (High Reflectivity)			LE	D	
Alumina Al ₂ O ₃ +ZrO ₂	Alumina Al ₂ O ₃	Alumina Al ₂ O ₃	Alumina Al ₂ O ₃	Alumina Al ₂ O ₃ +ZrO ₂	Single Cryst	
AZ211T	AO476K	AO476T	AO476A	AZ214T	SA1	00
_	96	96	96	_	_	
4.01	3.70	3.78	3.65	3.75	3.9	97
-	13.7	13.9	12.9	12.3	a-plane	22.5
650	350	380	360	450	a-plane c-axis	690
360	330	340	320	-	47	0
7.0	7.2	7.0	7.1	-	Parallel to c-axis	0.18
24	24	26	19	19	42	2
16	15	15	12	22.6	4:	3
>1014	>1014	>1014	>1014	>1014	>10) ¹⁴
10.8	9.4	9.6	9.2	9.6	Parallel to c-axis	11.5
2.7	4.0	3.0	2.1	2.0	Vertical to Axis c	9.3
-	86.7%	88.6%	91.0%	95.0%	-	
0.32~1.0	0.5~1.0	0.32~2.7	0.32~2.7	0.38~1.0	-	
Ra0.3 ~0.5µm	Ra0.2 ~0.3µm	Ra0.3 ~0.5µm	Ra0.3 ~0.5µm	Ra0.3 ~0.5µm	_	

 $^{^{\}star}$ Values are typical properties of each material, and may vary depending on product configurations or manufacturing processes. For more details, please feel free to contact us.



Thick Film Printing Substrates

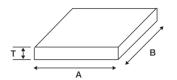
Available in large sizes or different shapes, suitable for thick film printing process

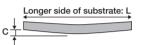
Features					7.5"×5.	5" (190.5×139.7mm)
 Standard Thickness Size flexibility to max * Scalable up to 1,28 	xmum: □300mm			in		
• Small through-hole (Ø0.2mm)	cutting				5	i" (127mm)
Standard Substrate Size:				4.5"	(114.3mm)	
Outer Dimension: 2"sq. / 3"sq. / 4"sq. 4.5"sq. / 5"sq. 7.5" × 5.5"			3" (76.2mm)	4" (101.6mm)		
Thickness (mm): 0.180						
0.254 0.381 0.508 0.635 0.762		2" (50.8mm)				
0.800 1.016 1.800						



Standard Substrate Specifications

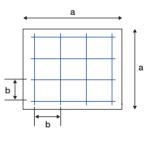
Material		AO476X	AO476T		
Size Availability (A,B)		12.7mm sq 152.4mm sq.	12.7mm sq □300mm		
Thickness A	Availability (T)	0.15~1.016mm	0.32~2.7mm		
Thickness Standard		±10% (minimum ±0.05mm)			
Tolerance	Premium	±7% (minimum ±0.05mm)			
As Fired Ca	mber (C)	0.3% of longer side of substrate 0.2% of longer side of substrate			
Surface Ro	ughness	Ra0.2-	-0.8µm		
Internal Void		×1500 ×400	×1500 ×400		

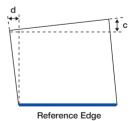


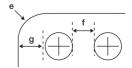


Standard Green-punching / Laser-cutting Specifications

Process	Gree	n Punching	Laser Cutting	
	Standard	±0.8% (minimum ±0.1mm)		
Substrate Dimensional Tolerance (a)	Premium	±0.5% (minimum ±0.08mm)	+0.20mm -0.05mm	
Totora los (a)	Super Premium	±0.25% (minimum ±0.05mm)		
0. 11	Standard	±0.8% (minimum ±0.1mm)	Edge to Scoreline:	
Singulation Scoring Tolerance (b)	Premium	±0.5% (minimum ±0.08mm)	+0.2/-0.05mm Scoreline to Scoreline	
Totora nov (c)	Super Premium	±0.25% (minimum ±0.05mm)	±0.05mm	
Parallelism (c) /	Standard	0.5% of outer dimension	±0.05mm	
Perpendicularity (d)	Premium	0.3% of outer dimension	±0.0311111	
Corner Radius (e)	0.51mm		_	
Hole Size	Round Hole: minimum 0.20mm diameter Square Hole: minimum 0.38mm square		_	
Spacing between Holes (f) / Spacing between Edge to Hole (g)	Same tolerance (minimu	_		







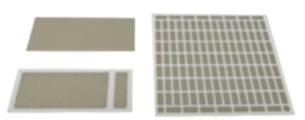


Alumina Metallized Substrates

Wide range of applications from circuit boards to power devices



- Available with high adhesion strength Mo-Mn
- Various options for conductive layer (incl. Ag or Cu)
- Customized pattern printing (Please consult us in advance regarding design)





- Circuit Board Substrates
- Power Device Substrates

■ Electrode pattern example









Long Thick Film Printing Substrates

Maximum 1250mm long substrate, with metallization option for pattern printing

Available Size

• 1250mm max × 125mm max × 0.635mm thick (Camber: 0.6mm / 500mm)





Thin Film Printing Substrates

Super smooth substrates used for thin film printed circuit boards

Features

- Excellent smoothness with less voids (Standard: Ra0.05~0.08µm)
- High mechanical strength
- Maximum available size: 165mm sq.



Standard Substrate Size

Outer Dimension:

2"sq. / 3"sq. / 4"sq.

 $4.5" \times 3.75" / 4.5$ "sq.

5"sq.

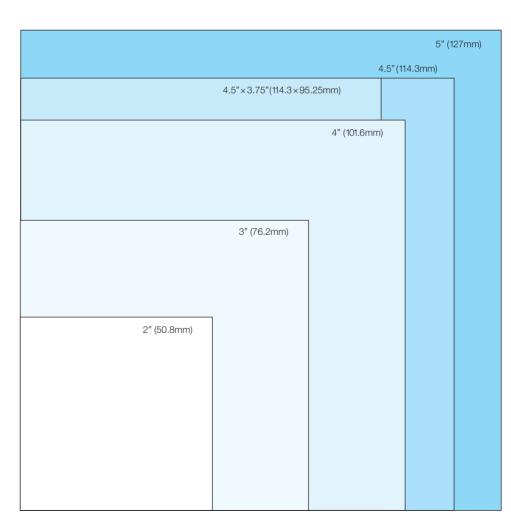
Thickness (mm):

0.100 / 0.127

0.200 / 0.254

0.381 / 0.500

0.635 / 1.000





Polished Thin Film Printing Substrates

Ceramic substrates contribute to the advancement and diversification of thin film technology

Features

- Dimensional stability at high temperature for multilayer thin film technology (for metal, glass or resin)
- Thin film quality improvement with high level of flatness and smoothness

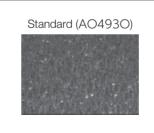


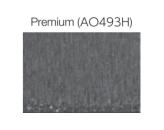
Low Voids Alumina Substrate (AO493H)

Features

- Best-in-class low voids, produced from tight process control
- Excellent surface smoothness
- Mitigation of electrical disconnection in thin film printed circuits

Internal Voids





Design Guideline

ltem	AO476T	AO493O	AO493H
Substrate Thickness (mm)	0.32~2.7	0.05~0.7	0.05~0.7
Flatness (mm)	0.05~0.6	0.05~0.4	0.05~0.4
Surface Roughness (Mirror Polish) (µm)	<ra0.05< th=""><th><ra0.02< th=""><th><ra0.01< th=""></ra0.01<></th></ra0.02<></th></ra0.05<>	<ra0.02< th=""><th><ra0.01< th=""></ra0.01<></th></ra0.02<>	<ra0.01< th=""></ra0.01<>

^{*} Values may vary depending on the size and thickness of substrates. Please contact us for further information.



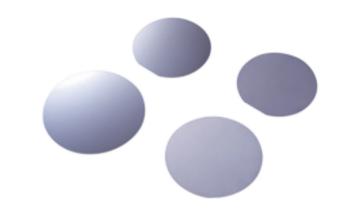
Single Crystal Sapphire Substrates

Base substrate applications for various epitaxies or depositions

The epitaxial growth of semiconductor film (e.g. Si, GaN, AlN, ZnO, etc.) requires a base substrate with similar lattice constant and no grain boundary. Single crystal sapphire with its smooth surface provides excellent performance, not only as the base substrate for LED, LD, SOS but also as a deposition substrate for super-conductive, metal, oxide, organic, or inorganic films.

Features

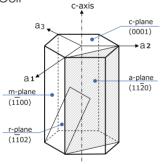
- Single crystal atomic layout
- Smooth surface finish with no grain boundary
- · High electrical insulation with low dielectric loss
- · Availability in customized crystal orientation
- High mechanical strength, heat resistance, chemical durability, and plasma resistance properties



(Unit: Å)

Crystal Orientation / Lattice

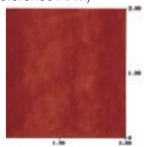




Lattice Constant (for reference)

Reference value	a-axis	c-axis		
Sapphire	4.758	12.991		
GaN	3.189	5.185		
InN	3.548	5.76		
Si	5.430	95		
GaAs	5.6533			
ZnO	3.252	5.213		
AIN	3.112	4.982		

Surface Roughness (reference AFM)



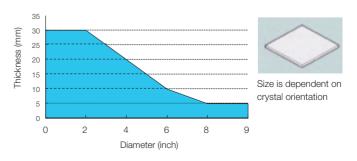
Standard Size

Standard Substrate Specification

* Please contact us for more details. (Unit: mm)

	, ,
Thickness	Orientation Flat Length
0.33 or 0.43 ±0.025	16 ±3
(Common for any) ±0.025	22 ±3
(Common for any) ±0.025	32.5 ±2.5
(Common for any) ±0.025	42.5 ±2.5
(Common for any) ±0.025	47.5 ±2.5
(Common for any) ±0.025	_
	0.33 or 0.43 ±0.025 (Common for any) ±0.025 (Common for any) ±0.025 (Common for any) ±0.025 (Common for any) ±0.025

Standard Size Availability





High Reflectivity Alumina Substrates

Contributing to improved LED efficiency, with both high reflectivity and high thermal conductivity

Features

 White ceramic substrate with both high reflectivity and high thermal conductivity

Reflectivity: 95%

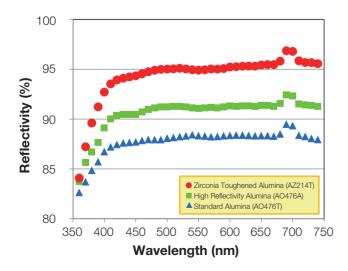
Thermal Conductivity: 19W/mk

- High level of dimensional accuracy by laser cutting
- Multiple pieces from a larger size substrate

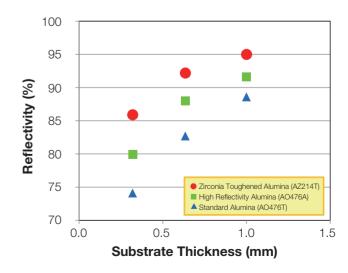
Applications

- Base substrate for LED sub-mount assembly for various types of LEDs such as down lights, tube lights, or bulbs
- LED sub-mount substrate for automotive applications

Reflectivity by Wavelength



Reflectivity by Substrate Thickness

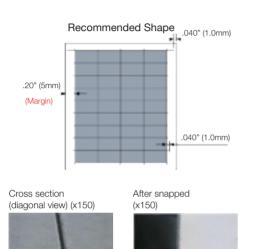




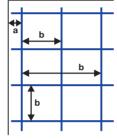
Reference

Laser Cutting Design Guideline

Scribe Line



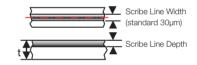
Substrate Edge



a = +.008" / -.002" (+0.20 / -0.05mm) $b = \pm .002" (\pm 0.05mm)$

Standard Depth (Inch (mm))

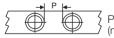
Substrate Thickness (t)	Scribe Line Depth
.015" (0.381)	.0051" (0.13)
.020″ (0.508)	.0067" (0.17)
.025" (0.635)	.0082" (0.21)
.030″ (0.762)	.0098" (0.25)
.032" (0.813)	.0102" (0.26)
.035" (0.889)	.0114" (0.29)
.040″ (1.016)	.0130" (0.33)
.047" (1.194)	.0157" (0.40)



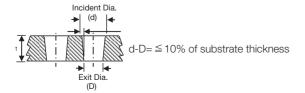
Through-Hole



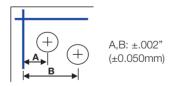
Through-F	Hole	Dimensional
Diameter	(D)	Tolerance
D ≤ Ø.03	0"	±.002"
(0.762mi	m)	(±0.050mm)
.030" ~ .10	00"	±.003"
(0.762mm) (2.5	54mm)	(±0.076mm)
D>.100	"	±.005"
(2.54mn	า)	(±0.127mm)



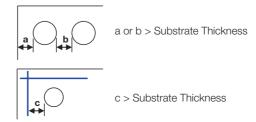
(more than substrate thickness to process)



■ Dimensional Tolerance from Scribe Line to Center of Through-hole



■ Locational Condition of Through-hole

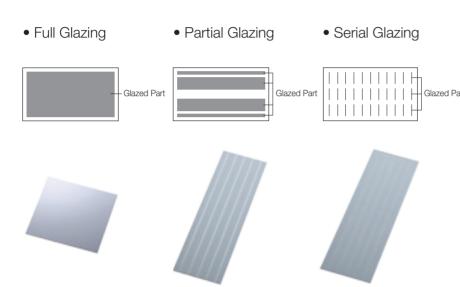




Optional

Glazing

Minimized surface defects enable precision thin film printing



■ Standard Glazing Specifications

		Full Glazing	Partial Glazing
Standard Thickness		45~80μm	30~60µm
Folerance	Standard	±15µm	±10µm
Tolera	Premium	±10µm	±7µm

Material Characteristics

* Values are typical data from test pieces

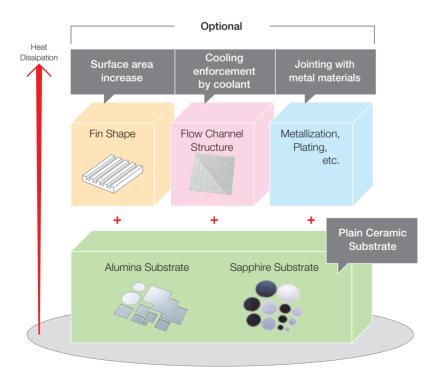
				typical data ironn toot piccoc
Item	Unit	Condition	GS-5	GS-71
Glass Transition Temperature	°C	DTA*	670	685
Glass Softening Temperature	°C	DTA*	865	870
Coefficient of Linear Thermal Expansion	1/°C	R.T.to 400°C	6.6 × 10 ⁻⁶	6.8 × 10 ⁻⁶
Thermal Conductivity	W/(m•K)	20°C	0.837	0.754
Volume Resistivity	Ω·cm	20°C 300°C 500°C	>10 ¹⁴ >10 ¹⁴ 2.8 × 10 ¹⁰	>10 ¹⁴ >10 ¹⁴ 2.1 × 10 ¹⁰
Dielectric Constant	-	1MHz	7.2	8.7
Dielectric Loss Tangent	-	1MHz	14.6 × 10 ⁻⁴	10.0 × 10 ⁻⁴
Surface Roughness	Ra µm		<0.02	<0.02

*DTA: Differential Thermal Analysis



Heat Dissipation Substrates

Thermal management is increasingly important as electronic devices evolve to realize further downsizing and improved functionality. Kyocera offers heat dissipation substrates to meet customers' needs by developing high thermal conductive materials, metal jointing technologies, or substrate configurations to improve dissipation efficiency.





Heat Dissipation Structure Ceramic Substrates

Monolithic ceramic structure with no bonding material for long-term reliability

Features

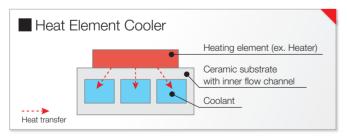
- Cooling or heat exchanging components made of light weight ceramic with low heat capacity provide a more efficient, energy saving system compared to metal
- Design possibility for thin wall or complex structure
- Long term, efficient cooling and temperature control
- Low maintenance cost due to superior chemical durability
- Applicational exploitation other than cooling or temperature control

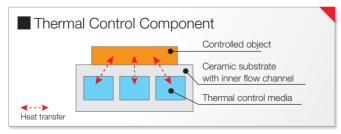


Applications

- Heat element coolers / Thermal control components Heat exchanger components
- Manifolds
 Micro reactors
 Thermal insulation components

Product Examples









Design Guideline for Flow Channel Structure

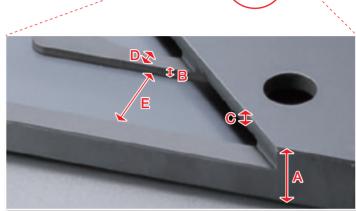
■ Standard Product Dimensions

(Unit: mm)

		Minimum	Maximum
А	Product Thickness	2	15
В	Channel Height	0.5	10
С	Lid Plate Thickness	0.5	_
D	Channel Wall Thickness	2	_
Е	Channel Width	1	12
D/E	Line & Space	>	0.2
B/D	Aspect Ratio	<	2.5
F	Maximum Size	600)sq.



^{*} Please contact us for more information



Material Characteristics

* Values are typical data from test pieces

			Unit	AO476T	AO479T	SC140A
Color			_	White	White	Black
Content			wt%	96	99.5	_
Bulk Density			_	3.7	3.9	3.1
	Vickers Hardness		GPa	13.9	16.3	23
Mechanical	Flexural Strength (3-pe	oint Bending)	MPa	380	470	450 (4-point Bending)
Characteristics	Young's Modules of E	lasticity	GPa	340	380	430
	Poisson's Ratio		-	0.23	0.23	0.17
	Thermal Conductivity		W/(m·K)	26	30	180
Thermal	Specific Heat Capacity	у	J/(g·K)	0.78	0.79	0.67
Characteristics	Coefficient of Linear Thermal Expansion	40-400°C	ppm/K	7	7.6	3.7
	Dielectric Strength		kV/mm	15	18	_
		RT		>1014	>1014	-
	Volume Resistivity	300°C	Ω·cm	1.0 × 10 ¹⁰	4.9 × 10 ¹⁰	_
Electrical		500°C		1.1 × 10 ⁸	3.5 × 10 ⁸	_
Characteristics	Dielectric Loss Tanger	nt	1MHz	3.0 × 10 ⁻⁴	1.0 × 10 ⁻⁴	-
	Dielectric Constant		1MHz	9.6	10.2	-

^{*}Other materials can also be considered upon request from prototyping





Functional Materials



Inductor Cores

Optimal materials and electrode patterns for customized applications and surface mounting processes

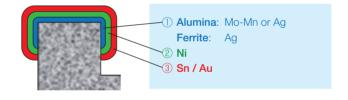
Features

- Core material either in alumina or in ferrite
- Flexible material selections for customized needs (ex. Magnetic permeability, Saturation magnetic flux density, Curie temperature, etc.)
- Accommodation to highly precise, miniaturized designs
- Electrode patterns adjustable to surface mounting process



■ Electrode Pattern Examples





Material Characteristics

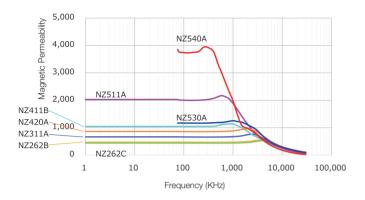
	Material Code		AO476X	NZ021A	NZ112H	NZ112A	NZ131A	NZ262C	NZ241A	NZ312B	NZ262B	
		100KHz	1	7	60	65	160	400	480	490	500	
	Magnetic Permeability	1MHz	1	7	58	65	160	400	480	500	500	
		10MHz	1	7	58	65	160	250	300	260	220	
		100KHz (×10 ⁻⁶)	-	26000	335	200	150	15	15	15	20	
	Relative Loss Factor (tan δ /μ)	1MHz (×10 ⁻⁶)	-	3600	625	130	80	30	30	60	50	
		10MHz (×10 ⁻⁶)	-	1300	1375	180	280	4000	2700	3200	5000	
	Relative Temperature Coefficient	-25-20°C (×10 ⁻⁶)	-	35	15	0	50	12	15	0	14	
	(αμγ)	20-80°C (×10 ⁻⁶)	-	35	8	0	35	17	7	-1	10	
	Saturation Magnetic Flux Density (mT)		-	140	360	380	370	470	350	290	430	
	Residual Magnetic Flux Density (mT)		-	60	150	230	160	300	120	110	150	
	Curie Temperature (°C)		-	≧300	≧300	≧300	240	300	150	90	220	
	Volume Resistivity (Ω·cm)		>1014	108	108	108	108	108	108	108	108	

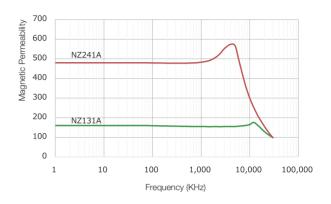
 $^{^{\}ast}$ If desired material is not on the list, please feel free to contact us.

^{*}Other patterns can also be considered upon request

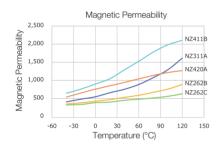


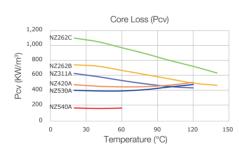
■ Magnetic Permeability vs Frequency

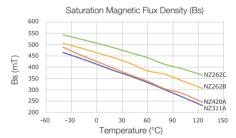




■ Magnetic Permeability / Core Loss (Pcv) / Saturation Magnetic Flux Density (Bs) vs Temperature







* Values are typical data from test pieces

values are typical data from teet p								
NZ350A	NZ301B	NZ311A	NZ420A	NZ411B	NZ511A	NZ530A	NZ540A	NZ550A
535	570	650	860	1100	2000	1150	3700	2000
550	600	650	880	1200	1500	1250	2000	(2000)
250	280	270	280	250	240	285	180	(250)
20	15	20	10	15	15	10	14	15
100	80	55	45	120	360	70	450	(250)
3400	3500	4500	4400	5300	9600	5350	180000	(7000)
2	0	20	5	15	7	8	3	_
-2	2	10	9	6	2	4	8	_
340	340	390	390	380	320	375	260	320
55	110	210	70	170	100	50	180	220
125	125	160	180	120	80	150	90	115
108	108	108	108	108	108	108	108	108



Inductor Core Shape Examples

SQUARE CORE

- Available in both alumina and ferrite materials
- Suitable for complex shape with tight tolerance
- Edged shape for high speed surface mounting



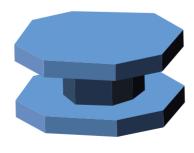
CAP CORE

- Thin wall cap shape suitable for shielded core
- Edged shape for high speed surface mounting
- Low height design possibility together with Push-pin Core
- Please contact us for possible combinations among OD, height, bottom thickness, and wall thickness.



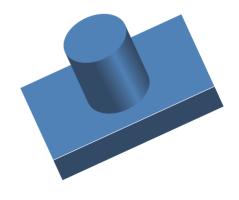
DR CORE (Edged sleeves & winding core type)

- Available in both alumina and ferrite materials
- Please contact us for possible combinations among OD, core diameter, height, machinable width, and sleeve thickness.



PUSHPIN CORE

- One side sleeve shape suitable for shielded core
- Low height design possibility together with Cap Core



^{*} Tooling structure for volume production may require some design restrictions.

Please contact us to finalize feasible dimensions and tolerances.



Piezoelectric PZT Substrates

PZT: Lead Zirconate Titanate Pb (Zr,Ti) O₃

Piezoelectric ceramic substrate with stable characteristics

Features

- Low voltage actuation with high piezoelectric constant
- High coercive electric field to mitigate piezoelectrical deterioration during high voltage actuation
- Excellent machinability (fine grains / minimal voids)

Applications

- Actuator components (positioning control)
- Various sensors



Design Guideline (mm)

MAX size: 120×90 MIN size: 30×30 Thickness: 0.1 - 9.0

* Please contact us for more details

Material Characteristics

* Values are typical data from test pieces

		Talace are typ.	cai data irom test pieces
Item	Unit	PZ0750	PZ0801
Bulk Density	-	7.9	7.9
Piezoelectric Constant (d15)	10 ⁻¹² m/V	750	900
Piezoelectric Constant (d31)	10 ⁻¹² m/V	-230	-190
Piezoelectric Constant (d33)	10 ⁻¹² m/V	450	400
Dielectric Constant $(\varepsilon_{11}^{T}/\varepsilon_{0})$	-	2400	3000
Dielectric Constant $(\varepsilon_{33}^{T}/\varepsilon_{0})$	-	1950	2280
Curie Temperature	°C	310	260
Coercive Electric Field	V/mm	1100	970





Device Peripherals



Sapphire Cover Plates

Surface protection from mechanical stress or friction for display and transparency

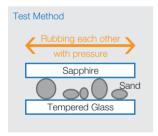
The LCD panel or reading indicator of an inspection stage requires a scratch-free protection plate with high optical transparency. Our unique design and polishing capabilities make our single-crystal sapphire into a thin, high-quality cover plate with remarkable hardness and stiffness.

Features

- Scratch-free hardness
- Excellent optical transparency
- Bonding technology with glass (sapphire on glass) for large, rigid substrates
- Assembly capability with surface coating or printing

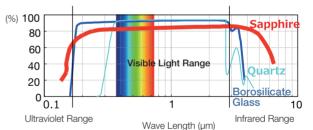


Scratch Resistance Test



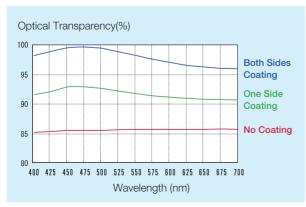


Optical Transparency



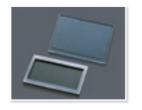
Options

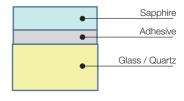
Anti-Reflection Coating (AR Coating)



SOG (Sapphire on Glass)

Sapphire-on-Glass bonding structure makes the plate both shock-resistant and shatter-resistant.





- * Please contact us for available sizes.
- * Values are typical properties of each material, and may vary depending on product configurations or manufacturing processes. For more details, please feel to contact us.



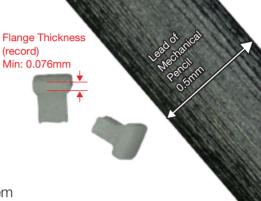
Volume Production Components for Various Electronics

Volume production capability of customized product, in monthly quantity of hundreds of millions per item

Features

- Variety of product configurations
 - Technology to optimize density balance in forming process enables multi-cavity shapes or ultra small components
- Wide selection of ceramics materials
 - Alumina / Silicon Carbide / Ferrite / etc.
- Volume production capability
 - Experience in monthly quantity of hundreds of millions per item
- Please contact us for any specific requirement

■ Ultra Small Component Example



Applications

• Insulators for downsized electronic components, or ceramic parts to minimize magnetic / dielectric losses (ex.: Used in or as fuses, thermostats, inductor cores, filters for base tranceiver stations, etc.)



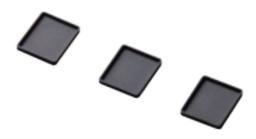


Ultra Thin Ceramic Caps

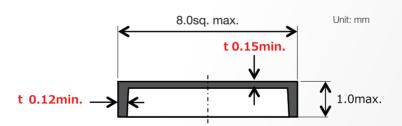
Ultra thin, enabling devices to become smaller in size, lower in height

Features

- Cap in ceramic for smaller size and lower height
- Ultra thin walls, based on Kyocera's unique material / forming technology





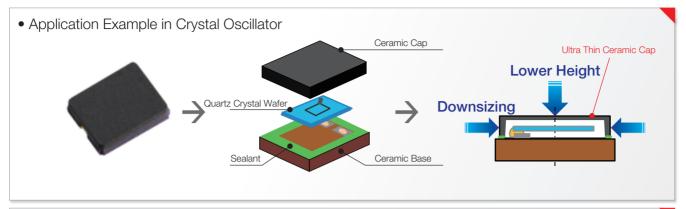


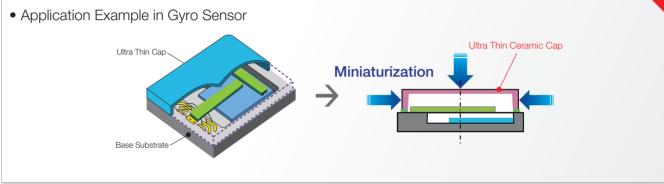
Minimum Wall Thickness Comparison (Compared to our company's product)

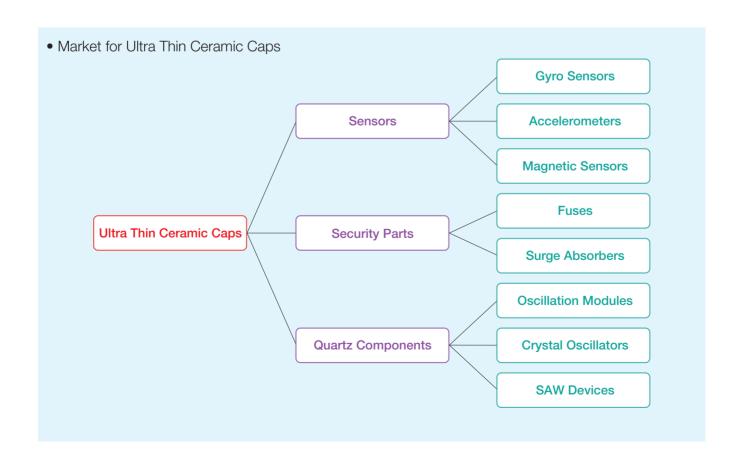
	Conventional Technology	New Technology
Side Wall Thickness	0.24mm	0.12mm
Top Wall Thickness	0.20mm	0.15mm

^{*} Please contact us for any other sizes.











High Voltage-resistant Alumina Ceramic (AH100A)

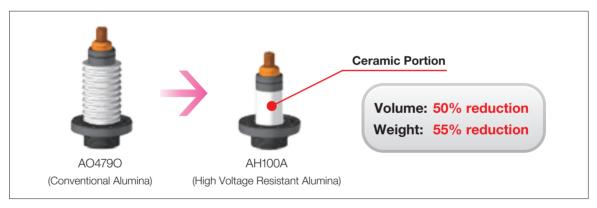
Possibility of 50% downsizing, with 1.6 times higher voltage resistance than conventional ceramic (based on Kyocera simulation)

Features

- Improvement of dielectric strength / creeping voltage resistance in vacuum atmosphere
- Conditioning time reduction at high voltage operation
- Ripple reduction
- 50% downsizing from conventional alumina (based on Kyocera simulation)



■ Design Image of Size Reduction



Applications

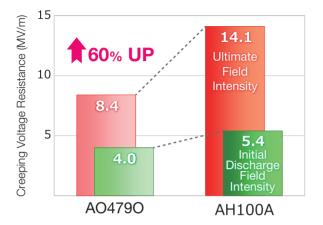
- High Voltage Accelerators (Analysis Equipment)
- Ultra High Vacuum Feedthroughs (Semiconductor Processing Tools)
- Electron Beam Generators (Medical or Industrial X-ray Tubes)

Conditioning Time Measuring Conditions: Pressure ≤ 10⁻³Pa Voltage Increase 1kV/min. Restarted from 0V every time flashover voltage is observed 100 AH100A 90 Time to reach 100kV 80 REDUCED BY 90% 70 Conventional Alumina 50 180 120 240 300 Time (min.)



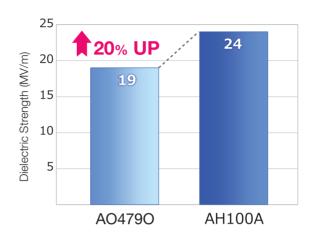
Creeping Voltage Resistance (in a vacuum)

Surface Distance 2mm Degree of Vacuum ≤ 10⁻⁴Pa Others per Kyocera testing set-up



Dielectric Strength

Bulk Ceramic Thickness 1mm Others based on JIS C 2141 standard



■ Material Characteristics & Measurement Comparison

		·		(Reference Data)
	Item	Unit	AO479O (Conventional Alumina)	AH100A (High Voltage Resistant Alumina)
	Ultimate Field Intensity	MV/m	8.4 (ave.)	14.1 (ave.)
	Dielectric Strength	MV/m	19	24
Electrical Characteristics	Volume Resistivity	Ω·cm	≧ 1 × 10 ¹⁴	≥1 × 10 ¹⁴
on ar action clies	Dielectric Constant (1MHz)	_	9.9	10.2
	Dielectric Loss Tangent (1MHz)	_	1 × 10 ⁻⁴	< 1 × 10 ⁻⁴
	Average Strength ASTM D2442 TYPE3	MPa	310	330
Mechanical	Young's Modulus of Elasticity	GPa	360	380
Characteristics	Poisson's Ratio	_	0.23	0.25
	Fracture Toughness	MPa·m¹/2	3~4	5
Thermal	Thermal Conductivity	W/(m·K)	29	24
Characteristics	Coefficient of Linear Thermal Expansion (RT-800°C)	ppm/°C	8.0	8.2



Characteristics of Kyocera's Fine Ceramics

The term "Fine Ceramics" is interchangeable with "advanced ceramics," "technical ceramics" and "engineered ceramics." Use varies by region and industry.

								- A !	Outlet			
			Ма	iterial					m Oxide			
Item			_		1015016	101150	101700		203)	101700	10.1701.1/10.1700	101000
	ial Code (New)				AO459K	A04450	AO4730	AO4760	AO4790	AO479S	AO479M/AO479G	
	terial Code (Old)				A459	A445	A473	A476	A479	A479S	A479M / A479G	A480S
Appea	pearance					T		De	nse			
Color					Russet	Dark Brown	White	White	White	Ivory	Ivory	Ivory
Conte	ntent (%)				89	90	92	96	99	99.5	99.5	99.7
					•High Frequency	Insulation •High Me	chanical Strength	Wear Resistant •H	igh Corrosion Resis	stance •High Temp	erature Resistance	
Main (Characteristics				•Good for Metallizing	Intercepting High Heat Dissipation	Metallizing High Mechanical Strength	Excellent Surface Finish Excellent Printability	High Hardness High Corrosion Resistance	High Hardness High Corrosion Resistance High Wear Resistance	High Hardness High Corrosion Resistance High Wear Resistance	High Purity High Corrosion Resistance Good Plasma Resistance High Wear Resistance
Main /	Applications				Magnetron	•IC Packages	Old Multilayer Packages Electron-tube Housing Wear Resistant Parts	Hybrid IC Substrates	Heat, Corrosion and Wear Resistant Parts	Corrosion and Wear Resistant Parts	Corrosion and Wear Resistant Parts Semiconductor Processing Equipment	Corrosion and Wear Resistant Parts Semiconductor Processing Equipment
Density	/		g/cm ³	JIS R1634	3.6	3.8	3.6	3.7	3.8	3.9	3.9	3.9
Water /	er Absorption % JIS C21				0	0	0	0	0	0	0	0
<	Vickers Hardness HV9.807N GPa			JIS R1610	12.1	12.7	12.3	13.7	15.2	16.0	15.7	17.2
lecha	Flexural Strength 3 P.B. M			JIS R1601	310	320	340	350	310	400	370	480
anica	Compressive Strength MPa			JIS R1608	-	2,430	2,300	2,992	2,160	2,350	2,984	2,900
유	<u> </u>			JIS R1602	280	320	280	320	360	370	370	380
Mechanical Characteristics	Poisson's Ratio			JIS R1602	0.23	0.23	0.23	0.23	0.23	0.23	0.23	0.23
ics	Fracture Toughness ((SEPB)	MPa·m ^{1/2}	JIS R1607	-	4.1	3.5	2.9	3 - 4	4	4.3	4.3
Ther	Coefficient of Linear	40 - 400°C	10.0/14	IIO D.1010	7.0	7.3	6.9	7.2	7.2	7.2	7.2	7.2
Thermal Characteristics	Thermal Expansion			JIS R1618	7.9	8.1	7.8	7.9	8.0	8.0	8.0	8.0
acte	Thermal Conductivity	20°C	W/(m·K)	JIS R1611	14	12	18	24	29	32	32	32
istic	Specific Heat Capacity	у	J/(g·K)	JIS R1611	0.75	0.75	0.78	0.78	0.79	0.78	0.78	0.79
Ø -	Thermal Shock Temperature (Put in Water, Relative Metho		°C	JIS R1648	-	150	150	150	150	180	180	180
	Dielectric Strength		KV/mm		15	12	16	15	15	15	15	15
		20°C			>1014	1011	>1014	>1014	>1014	>1014	>1014	>1014
ectric	Volume Resistivity	300°C	Ω·cm		1010	10 ⁷	1012	1010	1010	1013	1013	1013
<u>ài</u> C		500°C			108	10 ⁵	1010	108	108	1010	1010	1010
Electrical Characteristics	Dielectric Constant (1MHz)		-	JIS C2141	8.8	9.8	9.0	9.4	9.9	9.9	9.9	9.9
stics	Dielectric Loss Tangent (1MHz) (×10-4)		(×10 ⁻⁴)		6	20	6	4	2	1	1	1
	Loss Factor (×10 ⁻⁴)			52	190	54	38	20	10	10	10	
유 -	Nitric Acid (60%) 90	0°C,24H			-	1.17	0.32	0.02	0.10	0.00	0.01	0.05
Chemical Characteristics	Sulphuric Acid (95%) 95°C,24H (Weight Loss)			-	-	0.33	0.65	0.01	0.33	0.00	0.00	0.22
nical	Caustic Soda (30%) 80		mg/cm ²		_	0.58	0.91	0.86	0.26	0.00	0.00	0.04

^{*}The values are typical material properties and may vary according to products configuration and manufacturing process. For more details, please feel free to contact us.



								1		
Sapph	Sapphire Steatite		atite	Fors	sterite	Silicor	n Nitride	Alumini	um Nitride	Zirconia
(AI ₂ O	3)	(MgC)·SiO2)	(2Mg	O·SiO ₂)	(S	i ₃ N ₄)	(,	AIN)	(ZrO ₂)
SA10	00	SO2100	SO2110	F11200	F1023O	SN201B	SN2400	AN216A	AN2000	ZO201N
SA10	00	S210	S211	F1120	F1023	SN201B	SN240	AN216A	AN2000	Z201N
Dens	se	Der	Dense Dense		nse	Dense		Dense		Dense
Transpa	parent White Dark Brown Light Yellow		Yellow	Bla	ick	Gray	Ivory	Ivory		
99.9	9	-				-		-	99.9	-
Optical Trans Optical Trans High Heat Re High Freque Insulation	sparency esistance ency	Good Insulation Property	•Good Light Shield	Good Surface Finish	High Thermal Expansion	Wear Resistance	Excellent Thermal Shock Resistance		Insulation Property High Thermal Conductivity Lower Thermal Expansion High Purity Good Plasma	
High Chemi Resistance							High Strength, High Temperature Durability		Resistance	Excellent Surface Finish
Thin Film Su Windows Chemically Resistant Page		Various Circuit Parts		Resistor Cores Substrates for Resistors		Anti Wear Liner Pulverizer Molten Metal Parts Metal Forming Tool	Pulverizer Molten Metal Parts		arts Treatment Fixtures ocessing Equipment	•Industrial Cutlery •Pump Parts •Dies •Knives •Scissors •Wear Resistant Parts
3.97	7	2.8	3.1	3.0	3.0	3.2	3.3	3.4	3.2	6.0
0		0	0	0	0	0	0	0	0	0
a Plane	22.5	5.8	6.7	7.3	5.9	13.9	14.0	10.4	11.2	12.3
a Plane c Axis	690	190	220	180	160	580	1,020	310	220	1,000
2,94	0	1,305	-	-	-	3,160	3,551	3,200	2,900	3,000
470)	120	130	150	150	290	300	320	310	200
Parallel to Axis c Vertical to Axis c	0 10	0.22	0.22	0.24	0.24	0.28	0.28	0.24	0.24	0.31
2.1		1.9	-	-	-	4 - 5	7	3.2	2.5	6
Parallel to Axis c Vertical to Axis c	7.7	7.7	9.2	9.7	10.1	2.4	2.8	4.6	4.6	10.5
Parallel to Axis c Vertical to Axis c	0.0	8.0	10.4	-	-	3.2	3.3	5.3	5.2	11.0
42		2	3	5	5	25	27	150	67	3
0.75	5	0.75	0.72	0.78	0.75	0.64	0.65	0.71	0.72	0.46
180)	150	-	-	-	550	800	250	200	300
48		18	14	17	13	9.7	13	14	16	11
>101	14	>1014	>1013	>1014	>1014	>1014	>1014	>1014	>1014	1013
1012	2	1010	109	1013	10 ⁹	1012	1012	1010	1011	106
1011		10 ⁷	10 ⁷	1010	10 ⁹	1010	1010	108	10 ⁹	10³
Parallel to Axis c Vertical to Axis c		6	8	6.5	6.5	8.9	9.6	8.6	8.5	33.0
<1		18	750	3	5	17.0	19	3	2	16
-		108	6,000	20	30	-	-	26	17	520
≑0.00)	0.01	-	-	-	-	1.11	-	-	≑0.00
≑0.0 0)	0.00	-	-	-	-	0	-	-	0.04
≑0.00)	15.35	-	-	-	-	0.22	-	-	0.08
1kaf/mm²=0										

¹kgf/mm²=9.807MPa



KYOCERA Corporation

Corporate Fine Ceramics Group

https://global.kyocera.com/prdct/fc/

Kyocera Fine Ceramics





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